

# Mitsubishi 6<sup>th</sup> gen CSTBT 1200V CM450DY-24S IGBT Power Module

## Reverse Costing Analysis

### Physical Analysis of the Device

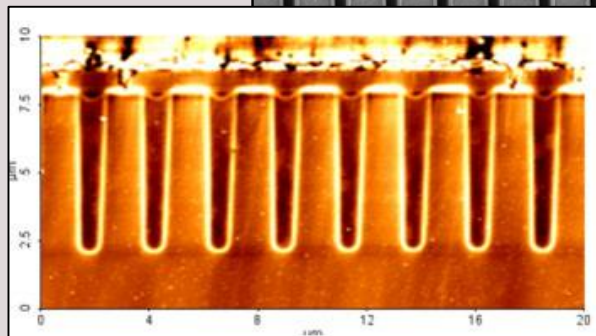
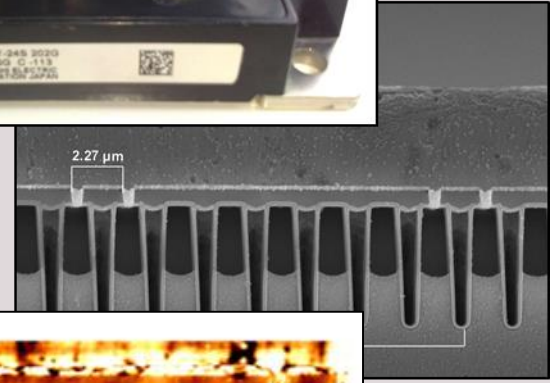
#### Step by Step Reconstruction of the Process Flow

#### Cost of Manufacturing & Estimation of Selling Price

System Plus Consulting is pleased to publish a new version of the reverse costing report on the 6th generation of CSTBT from MITSUBISHI. SCM and SRP profiles has been added to provide more information on the location and concentrations of dopants. Discover the first IGBT with 2 metals for the emitter. Based on a complete teardown process, the report provides an estimation of the production cost as well as the selling price of the CSTBT device and the CM450DY-24S, 1200V 450A, half-bridge IGBT module.

This report provides a reverse costing of the POWER TRANSISTOR and POWER MODULE with:

- Detailed photos & Material analysis
- Manufacturing Process Flow
- SCM and SRP profiles
- In-depth economical analysis
- Manufacturing cost breakdown
- Selling price estimation



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